

TOSHIBA

2SC3334

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC3334

HIGH VOLTAGE SWITCHING APPLICATIONS.

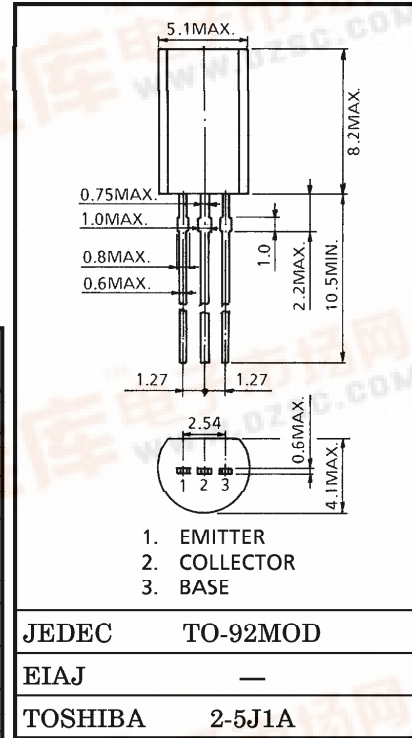
COLOR TV CHROMA OUTPUT APPLICATIONS.

- High Voltage : $V_{CEO} = 250V$
- Low C_{re} : 1.8pF (Max.)
- Complementary to 2SA1321

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	250	V
Collector-Emitter Voltage	V_{CEO}	250	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	DC	I_C	50
	Pulse	I_{CP}	100
Base Current	I_B	20	mA
Collector Power Dissipation	P_C	0.9	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

Unit in mm



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB} = 200V, I_E = 0$	—	—	1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	250	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = 20V, I_C = 25mA$	50	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$	—	—	1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 20V, I_C = 25mA$	—	0.75	—	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 10mA$	60	100	—	MHz
Reverse Transfer Capacitance	C_{re}	$V_{CB} = 30V, I_E = 0, f = 1MHz$	—	—	1.8	pF

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